

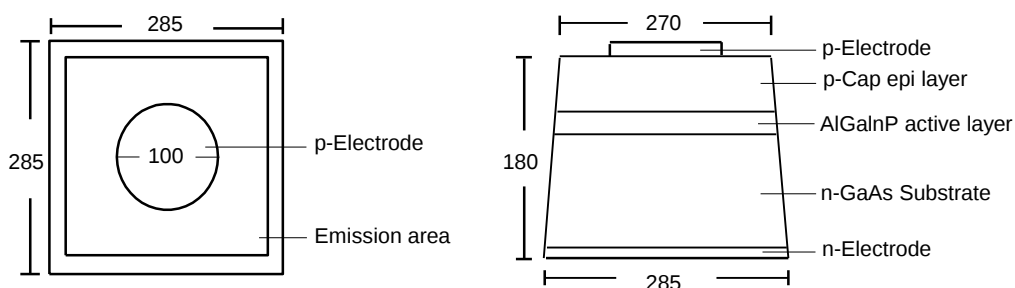
■ Features :

- MOVPE epi wafer
- Suitable for new creative products

■ Typical Applications :

- SMD Chip LED
- Backlight
- Equipment indicators
- Message Boards
- Commercial Applications

■ Outline Dimensions : (Unit: μm)



■ Physical Structure :

Chip dimension	Chip size	285 μm x 285 μm
	Thickness	180 μm
	Emission area	270 μm
	Bonding pad	100 μm
Electrode	Top: P (anode)	Gold (Aluminum optional)
	Backside: N (cathode)	Gold alloy
Surface condition	Frosted	

■ Electro-Optical Characteristics : ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	$I_F = 20 \text{ mA}$	-	2.05	2.40	V
Reverse Voltage	V_R	$I_R = 10 \text{ uA}$	5	-	-	V
Wavelength	λ_P	$I_F = 20 \text{ mA}$	-	-	-	nm
	λ_d		589	594	599	
Spectral width at half height	$\Delta \lambda$	$I_F = 20 \text{ mA}$	-	20	-	nm
Luminous Intensity	I_V	$I_F = 20 \text{ mA}$	240	-	-	mcd

■ Typical Electro-Optical Characteristics Curve:

Fig 1. Forward Current vs. Forward Voltage

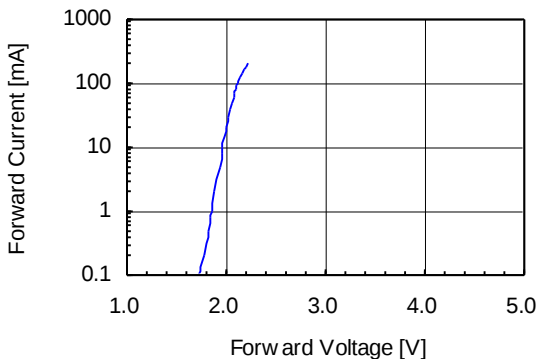


Fig 2. Relative Intensity vs. Forward Current

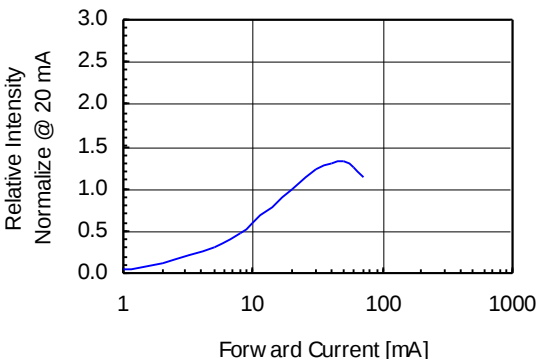


Fig 3. Forward Voltage vs. Temperature

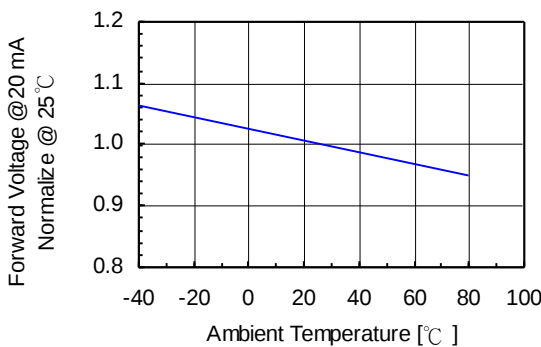


Fig 4. Relative Intensity vs. Temperature

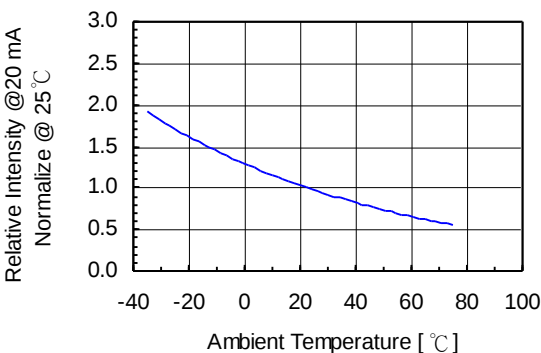


Fig 5. Relative Intensity vs. Wavelength

